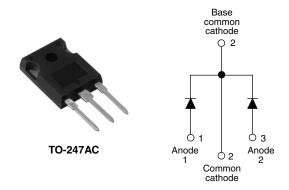


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 6 A



PRODUCT SUMMARY					
V_{R}	1200 V				
V _F at 6 A at 25 °C	3.0 V				
I _{F(AV)}	2 x 6 A				
t _{rr} (typical)	26 ns				
T _J (maximum)	150 °C				
Q _{rr} (typical)	116 nC				
dl _{(rec)M} /dt (typical) at 125 °C	100 A/μs				
I _{RRM} (typical)	4.4 A				

FEATURES

- · Ultrafast recovery
- · Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Designed and qualified for industrial level

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

HFA12PA120C is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. The HFA12PA120C has basic ratings of 1200 V and 6 A per leg continuous current. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current ($I_{\mbox{\scriptsize RRM}}$) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA12PA120C is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_R		1200	V	
Maximum continuous forward current	´ l _F	T _C = 100 °C	6		
per dev			12	Α	
Single pulse forward current	I _{FSM}		80	A	
Maximum repetitive forward current	I _{FRM}		24		
Maximum power dissination	P _D	T _C = 25 °C	62.5	W	
Maximum power dissipation		T _C = 100 °C	25	VV	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

HFA12PA120C

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ		-	-	
		I _F = 6 A	-	2.7	3.0	V
Maximum forward voltage V _{FM}	I _F = 12 A	-	3.5	3.9		
	I _F = 6 A, T _J = 125 °C	-	2.4	2.8		
Maximum reverse I _{RM}		$V_R = V_R$ rated	-	0.26	5.0	
		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	110	500	μΑ
Junction capacitance	C _T	V _R = 200 V	-	9.0	14	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body -		8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	26	-	
Reverse recovery time	t _{rr1}	T _J = 25 °C	I _F = 6 A dI _F /dt = 200 A/μs V _R = 200 V	-	53	80	ns
	t _{rr2}	T _J = 125 °C		-	87	130	
Peak recovery current I Reverse recovery charge	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A nC
	I _{RRM2}	T _J = 125 °C		-	5.0	9.0	
	Q _{rr1}	T _J = 25 °C		-	116	320	
	Q _{rr2}	T _J = 125 °C		-	233	585	
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	180	-	- A/μs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	100	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	2.0	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount -		-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-	
Majaht			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC (JEDEC)	HFA12PA120C			

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HEXFRED® Vish Ultrafast Soft Recovery Diode, 2 x 6 A

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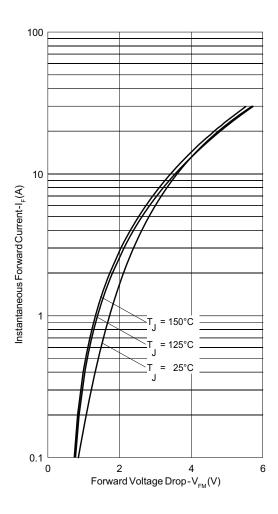


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

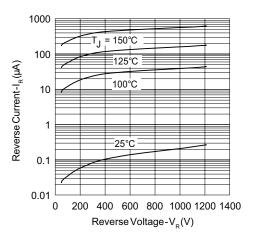


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

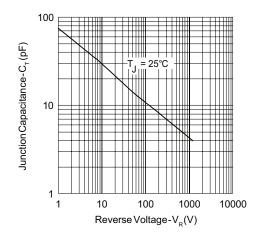


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

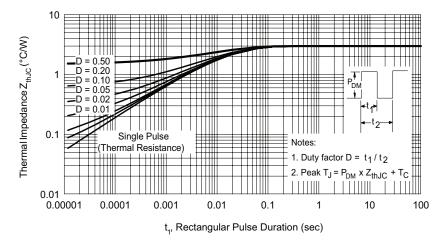


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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HEXFRED® Ultrafast Soft Recovery Diode, 2 x 6 A



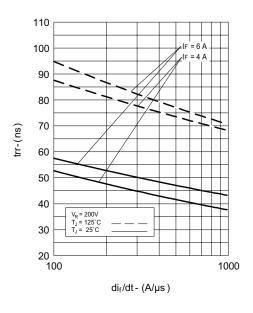


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

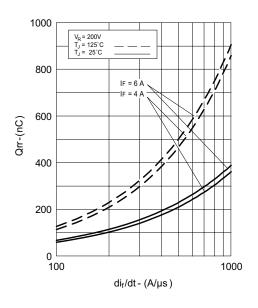


Fig. 7 - Typical Stored Charge vs. dl_F/dt

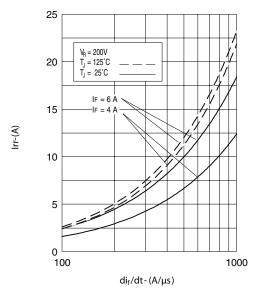


Fig. 6 - Typical Recovery Current vs. dI_F/dt

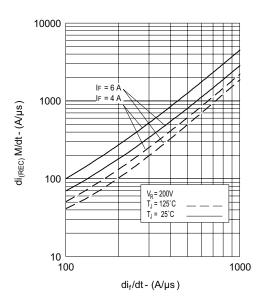


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 2 x 6 A

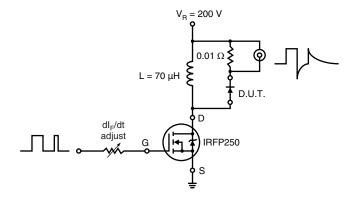
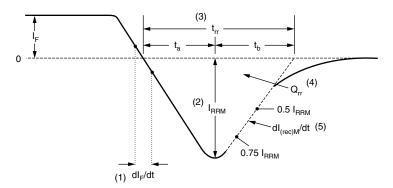


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $\begin{array}{l} \text{(3) } \textbf{t}_{\text{rr}} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through 0.75 I}_{\text{RRM}} \text{ and 0.50 I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

HFA12PA120C

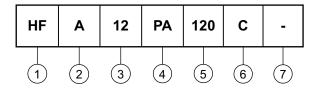
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ORDERING INFORMATION TABLE

Device code



- 1 HEXFRED® family
- 2 Process designator: A = Subs. electron irradiated

B = Subs. platinum

- 3 Current rating (12 = 12 A)
- 4 Package outline (PA = TO-247, 3 pins)
- 5 Voltage rating (120 = 1200 V)
- 6 Configuration (C = Center tap common cathode)
- 7 • None = Standard production
 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95223				
Part marking information	http://www.vishay.com/doc?95226			

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